Electrical Characteristics of the IGBT T_j= 25 unless otherwise specified

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit

Electrical Characteristics of the Diode T_j= 25 unless otherwise specified

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Diode Forward Voltage	V_F	I_F= 40A T_j= 25°C, T_j= 125°C T_j= 150°C		2.00 1.90 1.80	2.60	V

Electrical Characteristics of the DIODE

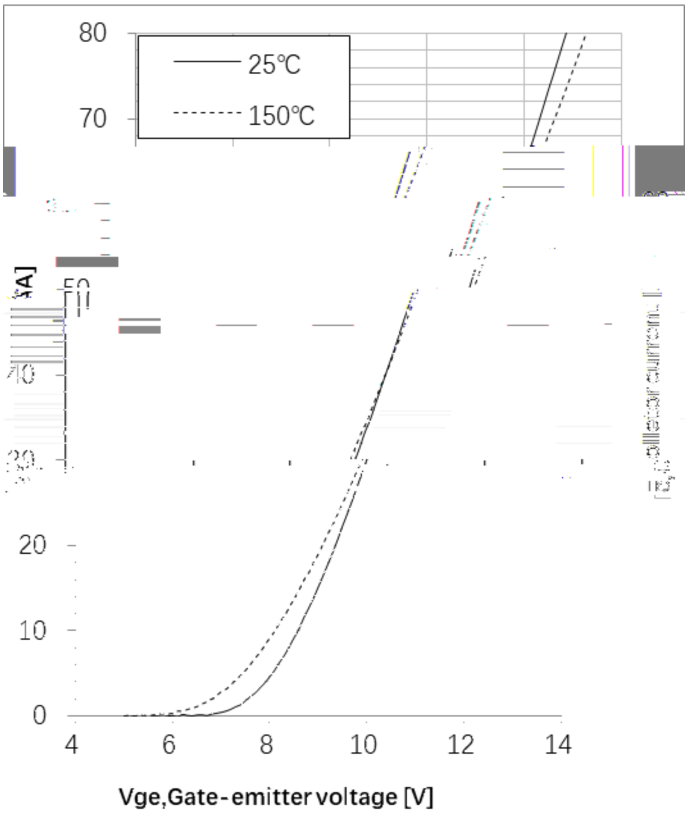
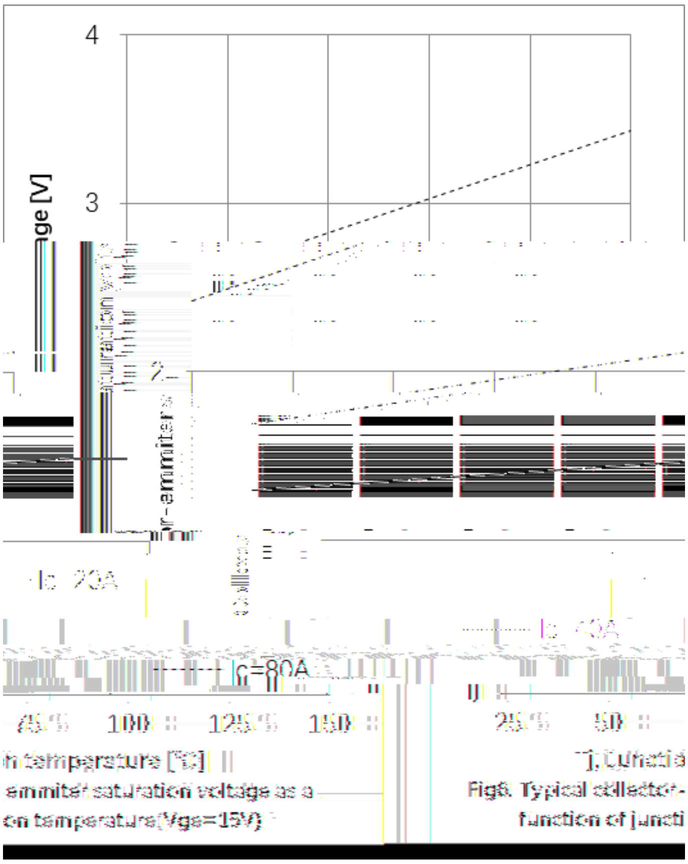
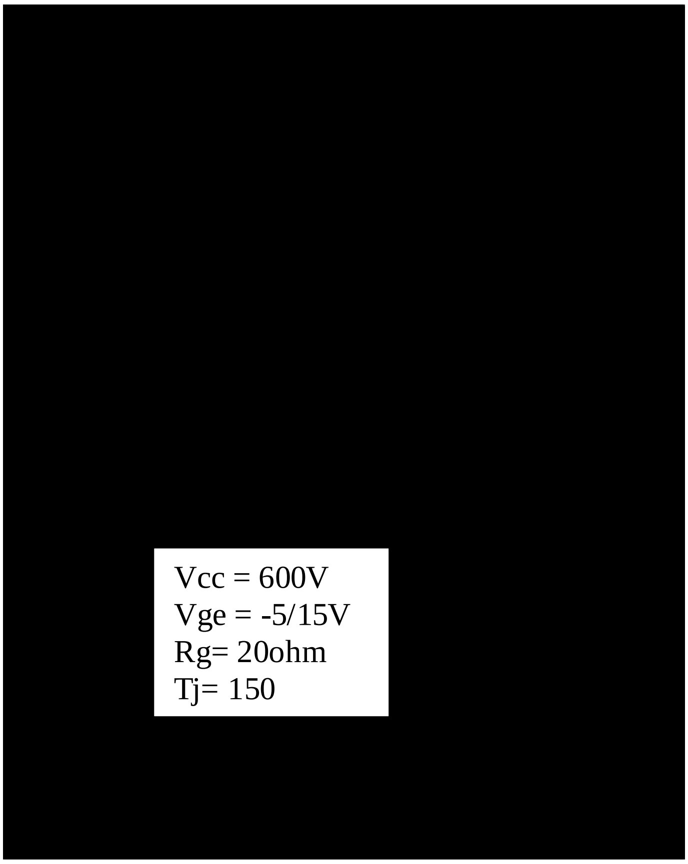
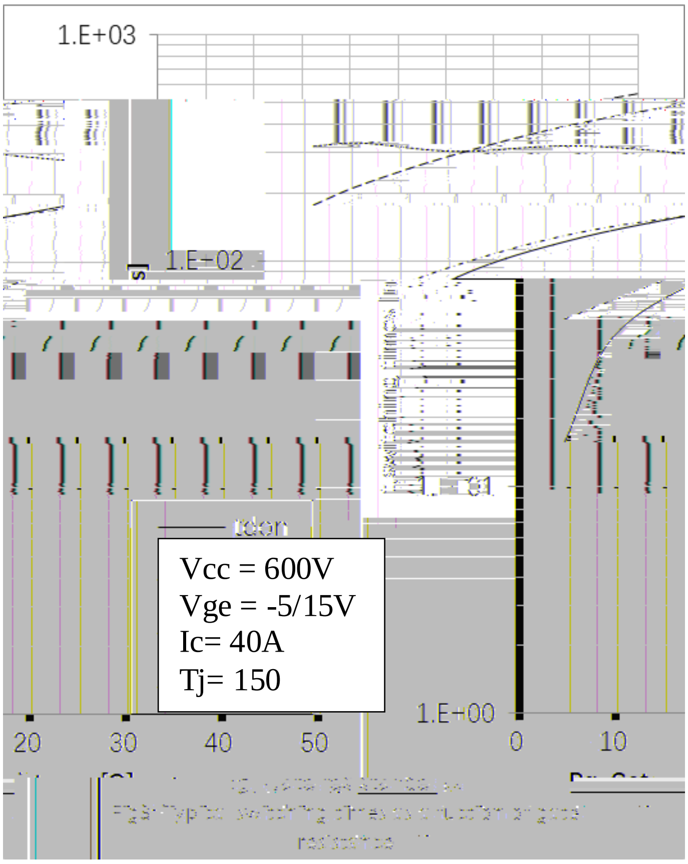


Fig5. Typical transfer characteristic (Vce=20V)







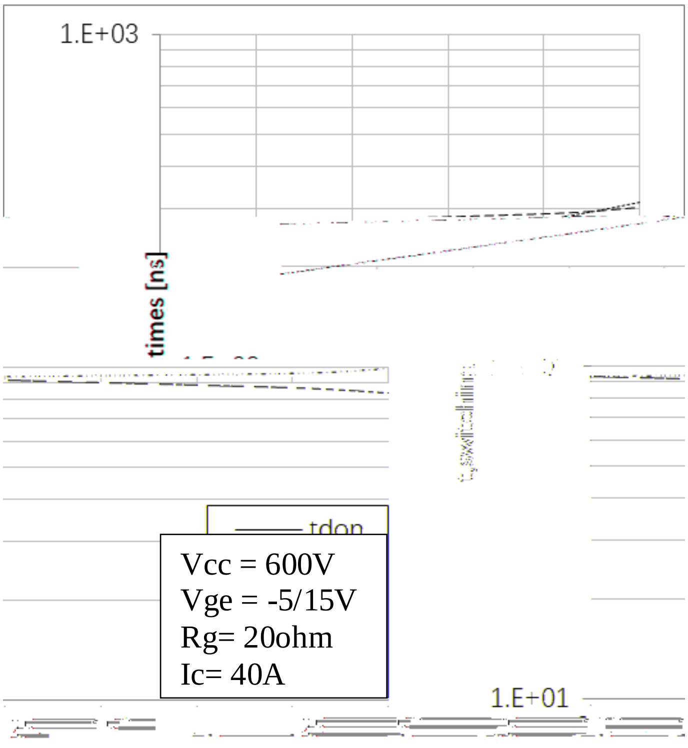


Fig9. Typical switching times as a fuction of junction temperature

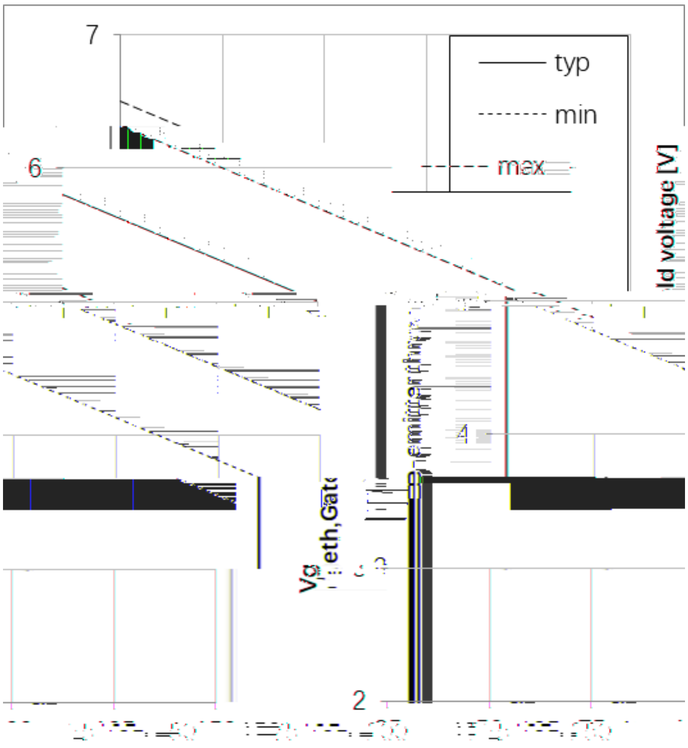


Fig10. Gate-emitter threshold voltage as a fuction of junction temperature

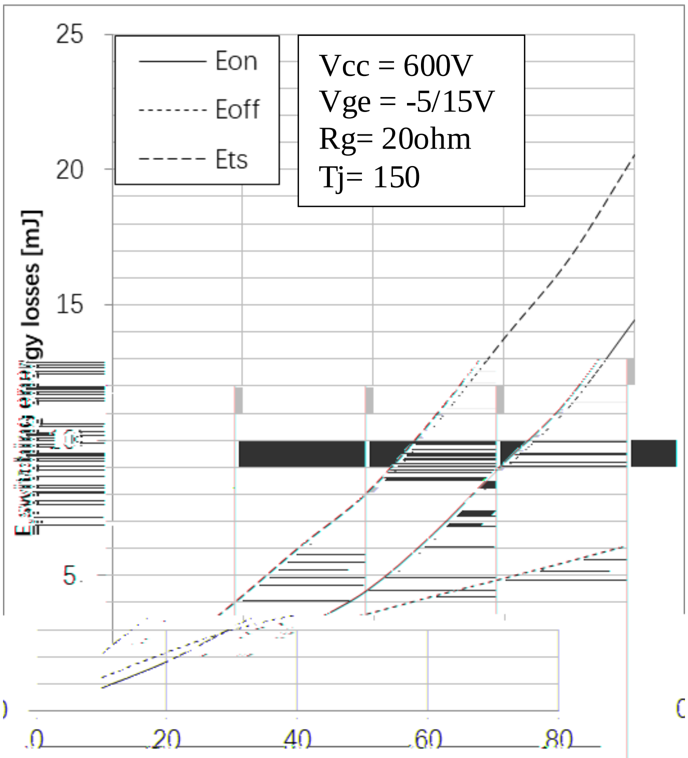


Fig11. Typical switching energy losses as a fuction of collector current

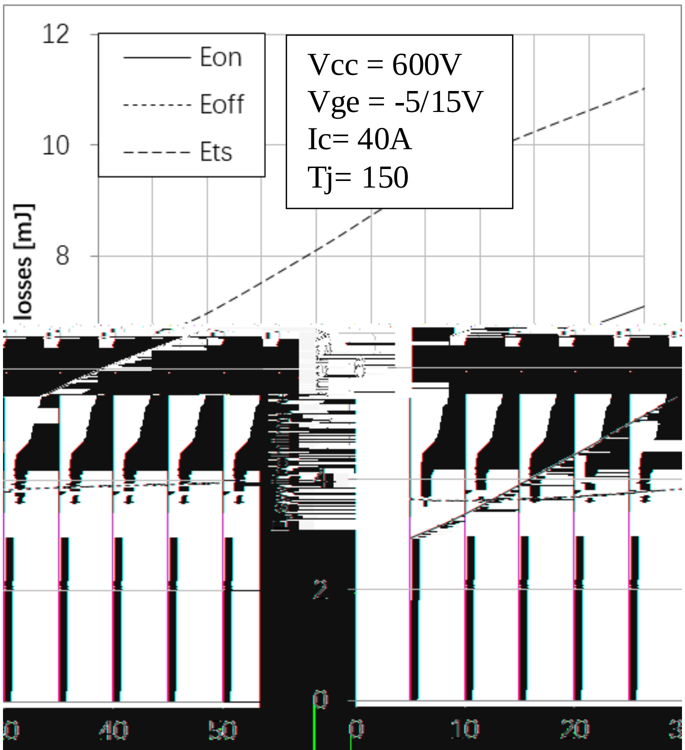
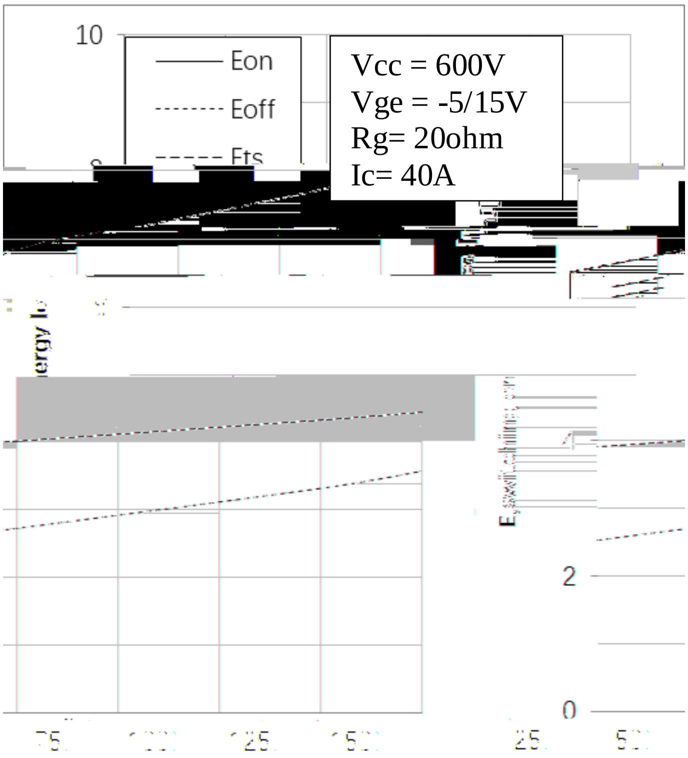


Fig12. Typical switching energy losses as a fuction of gate resistance



ion temperature [°C] Tj, Junct

ing energy losses as a fuction of Fig13. Typical switch

tion temperature func

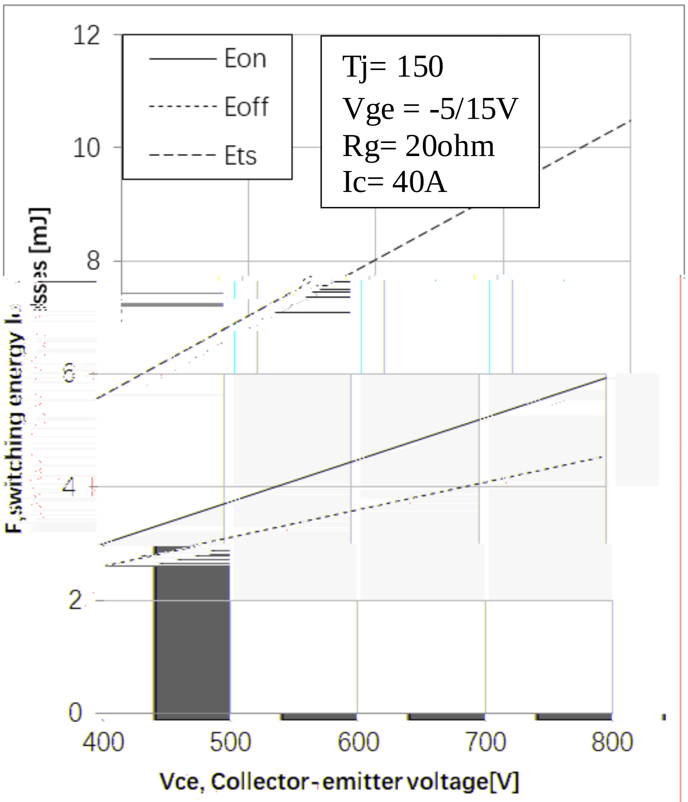


Fig14. Typical switching energy losses as a fuction of collector-emitter voltage

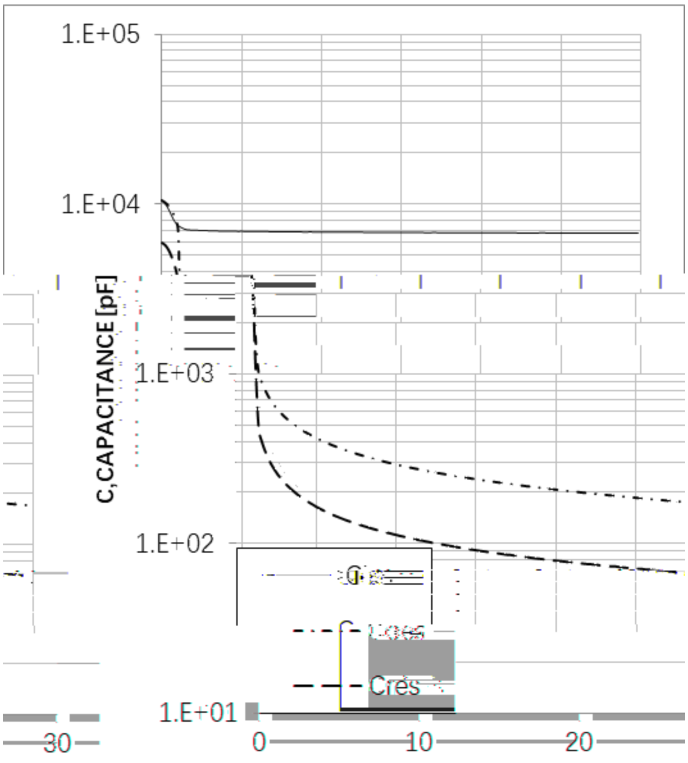


Fig15. Typical capacitance as a function of collector emitter voltage

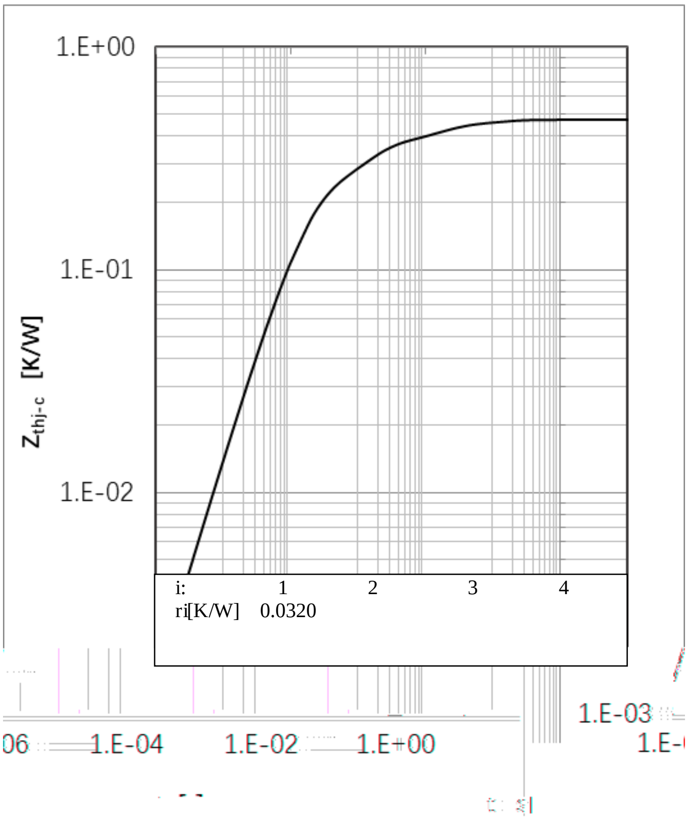
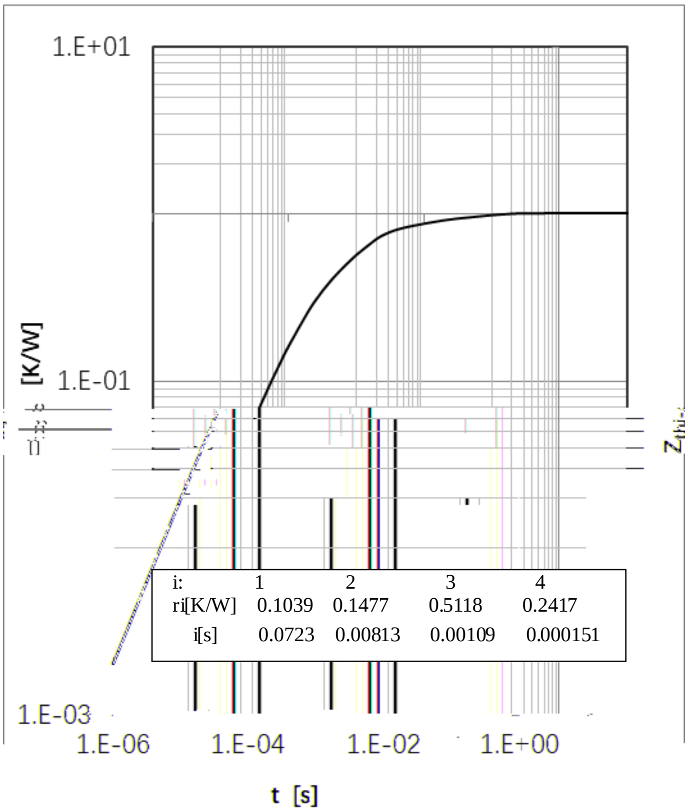


Fig 16. IGBT Transient Thermal Impedar



i:	1	2	3	4
ri[K/W]	0.1039	0.1477	0.5118	0.2417
i[s]	0.0723	0.00813	0.00109	0.000151

[illegible]

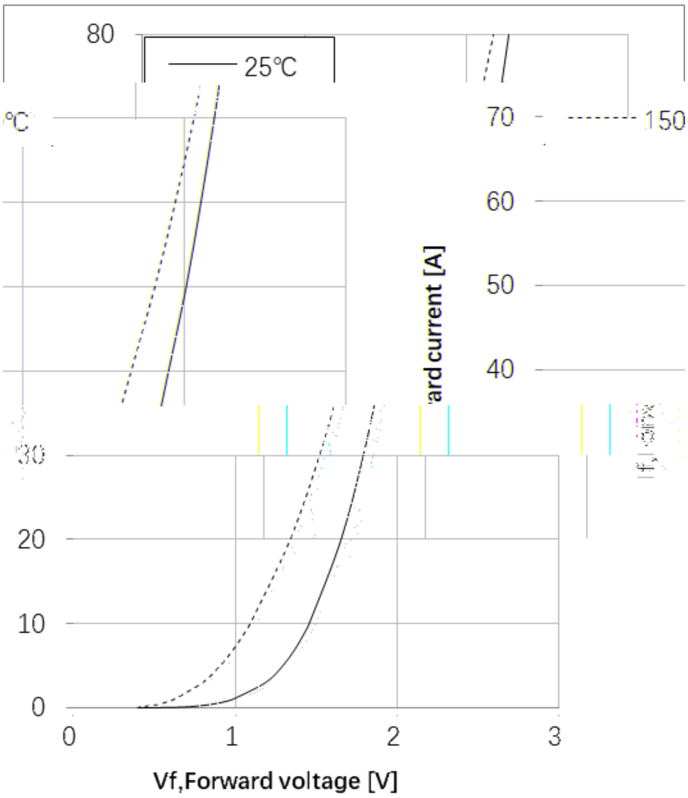
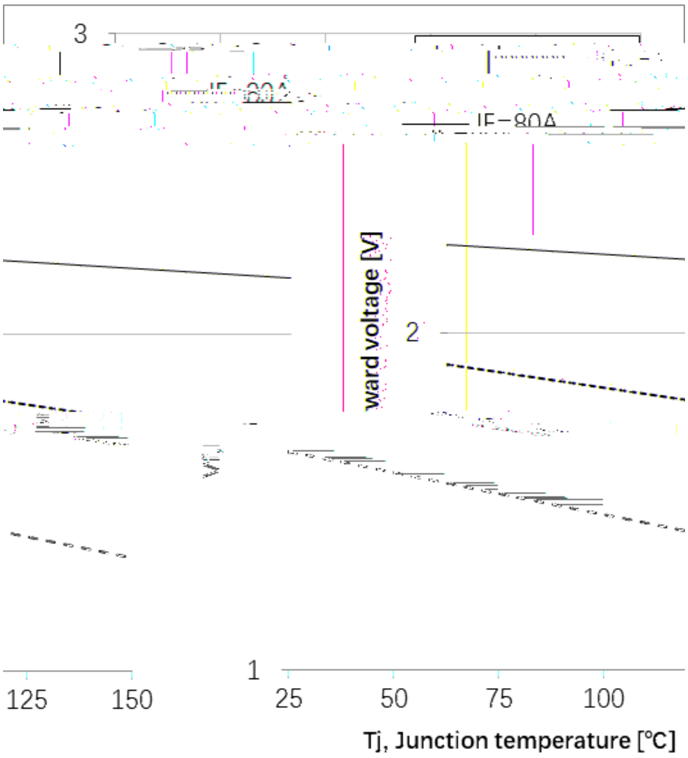


Fig18. Diode forawrd current as a function of foraward voltage



f junction

Fig19. Diode forawrd voltage as a function c temperature